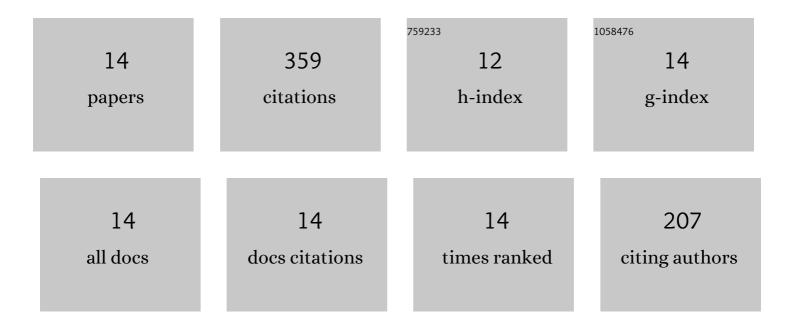
Vibhor Kumar

List of Publications by Year in descending order

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#	Article	IF	CITATIONS
1	Barrier height inhomogeneities induced anomaly in thermal sensitivity of Ni/4H-SiC Schottky diode temperature sensor. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2014, 32, .	1.2	55
2	Epitaxial 4H–SiC based Schottky diode temperature sensors in ultra-low current range. Vacuum, 2020, 182, 109590.	3.5	46
3	Capacitance rollâ€off and frequencyâ€dispersion capacitance–conductance phenomena in field plate and guard ring edgeâ€terminated Ni/SiO ₂ /4Hâ€nSiC Schottky barrier diodes. Physica Status Solidi (A) Applications and Materials Science, 2016, 213, 193-202.	1.8	39
4	Excellent UV-Light Triggered Photocatalytic Performance of ZnO.SiO2 Nanocomposite for Water Pollutant Compound Methyl Orange Dye. Nanomaterials, 2021, 11, 2548.	4.1	38
5	Diameter dependent thermal sensitivity variation trend in Ni/4H-SiC Schottky diode temperature sensors. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2015, 33, .	1.2	34
6	Electronic transport in epitaxial 4H–SiC based Schottky diodes modified selectively by swift heavy ions. Materials Science in Semiconductor Processing, 2020, 115, 105108.	4.0	26
7	Tailoring Surface and Electrical Properties of Ni/4Hâ€nSiC Schottky Barrier Diodes via Selective Swift Heavy Ion Irradiation. Physica Status Solidi (A) Applications and Materials Science, 2018, 215, 1700555.	1.8	24
8	Defect levels in high energy heavy ion implanted 4H-SiC. Materials Letters, 2022, 308, 131150.	2.6	18
9	Interface improvement of epitaxial 4H-SiC based Schottky didoes by selective heavy ion irradiation. Applied Nanoscience (Switzerland), 2023, 13, 221-228.	3.1	17
10	Investigation of structural and impedance spectroscopic properties of borate glasses with high Li+ concentration. Solid State Ionics, 2021, 368, 115704.	2.7	17
11	Selective SHI irradiation for mesa type edge termination in semiconductor planar junction. Journal of Physics: Conference Series, 2013, 423, 012057.	0.4	15
12	Interfacial and structural analysis of MeV heavy ion irradiated SiC. Applied Nanoscience (Switzerland), 2023, 13, 3181-3188.	3.1	15
13	Improvement in reverse bias leakage current of Ni/4H-nSiC Schottky barrier diodes via MeV selective ion irradiation. IOP Conference Series: Materials Science and Engineering, 2018, 331, 012016.	0.6	12
14	LnFe0.5Cr0.5O3 based perovskites showing multiferroic properties and polarization induced photoelectrochemical activity. Journal of Solid State Chemistry, 2021, 299, 122200.	2.9	3